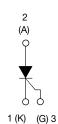
VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

High Voltage Phase Control Thyristor, 16 A





3L TO-220 FullPAK

PRIMARY CHARACTERISTICS					
I _{T(AV)}	10 A				
V _{DRM} /V _{RRM}	800 V, 1200 V				
V_{TM}	1.4 V				
I _{GT}	60 mA				
T _J	-40 °C to 125 °C				
Package	3L TO-220 FullPAK				
Circuit configuration	Single SCR				

FEATURES

- · Designed and qualified for industrial level
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL pending
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS..FP... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS			
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	10	Δ.		
I _{RMS}		16	Α		
V _{DRM} /V _{RRM}		800, 1200	V		
I _{TSM}		200	A		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ	Range	-40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-16TTS08FP-M3	800	800	10			
VS-16TTS12FP-M3	1200	1200	10			



VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	
PARAMETER	STINIBUL		TEST CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I _{T(AV)}	$T_{\rm C} = 70 ^{\circ}{\rm C}, 1$	80° conduction, half sine wave	1	0	
Maximum RMS on-state current	I _{RMS}			1	6	Α
Maximum peak, one-cycle,	I	10 ms sine p	ulse, rated V _{RRM} applied	1	70	A
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	2	00	
Maximum I ² t for fusing	l ² t	10 ms sine p	ulse, rated V _{RRM} applied	14	44	A ² s
Maximum 1-t for fusing	1-1	10 ms sine p	10 ms sine pulse, no voltage reapplied		00	7 A ^z S
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied		000	A²√s
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1	.4	٧
On-state slope resistance	r _t	T _{.1} = 125 °C		24	1.0	mΩ
Threshold voltage	V _{T(TO)}	1j=125 C	I _J = 125 °C		.1	V
Maximum rayaraa and direct lookage current	1 /1	T _J = 25 °C	V - Reted V A	0	.5	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$T_J = 125 ^{\circ}\text{C}$ $V_R = \text{Rated } V_{RRM}/V_{DRM}$		1	0	
Holding current	l _H	Anode supply = 6 V, resistive load, initial I _T = 1 A 16TTS08FP, 16TTS12FP, T _J = 25 °C		-	150	mA
Maximum latching current	IL	Anode supply = 6 V, resistive load, T _J = 25 °C 200		00		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 \text{ %, } V_{DRM} = R_g - k = Open$		5	00	V/µs
Maximum rate of rise of turned-on current	dI/dt			1:	50	A/µs

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0] vv
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = -10 °C	90	mA
		Anode supply = 6 V, resistive load, T _J = 25 °C	60	
		Anode supply = 6 V, resistive load, T _J = 125 °C	35	
		Anode supply = 6 V, resistive load, T_J = -10 $^{\circ}$ C	3.0	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = 25$ °C	2.0	V
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	\ \
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Peted value	0.25	
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T. = 195 °C	4	μs
Typical turn-off time	tq	T _J = 125 °C	110	



Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	2.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
	maximum			12 (10)	(lbf · in)
		Case style 3L TO-220 FullPAK	16TTS	08FP	
Marking device				16TTS	12FP

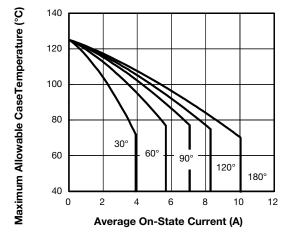


Fig. 1 - Current Rating Characteristics

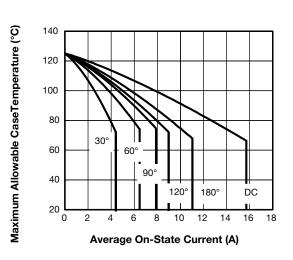


Fig. 2 - Current Rating Characteristics

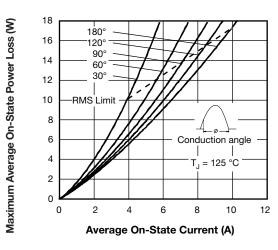


Fig. 3 - On-State Power Loss Characteristics

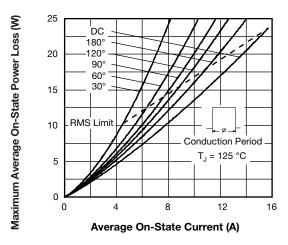
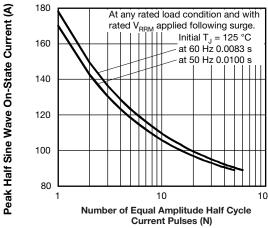


Fig. 4 - On-State Power Loss Characteristics



www.vishay.com

Vishay Semiconductors





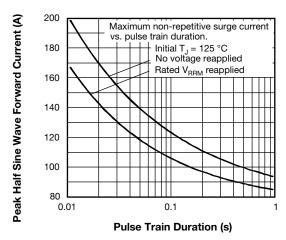
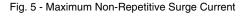


Fig. 6 - Maximum Non-Repetitive Surge Current



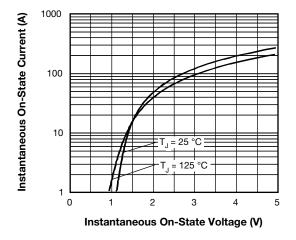


Fig. 7 - On-State Voltage Drop Characteristics

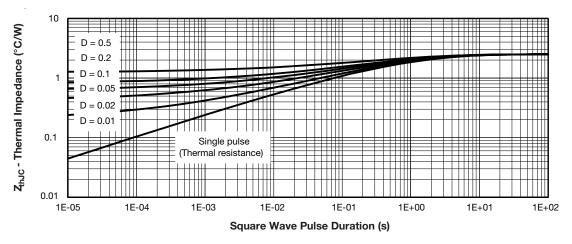


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

VS-16TTS08FP-M3, VS-16TTS12FP-M3

Vishay Semiconductors

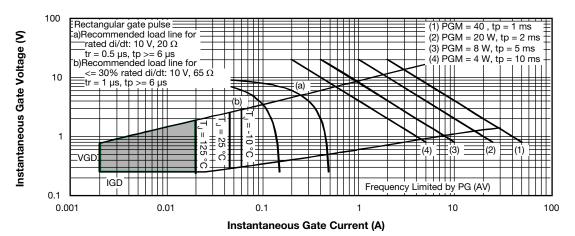


Fig. 9 - Gate Characteristics

v

ORDERING INFORMATION TABLE

VS-**Device code** 16 Т Т S 12 FP -M3 (2) (3)(4) (5) (6) (7)8 Vishay Semiconductors product Current rating, RMS value Circuit configuration: T = single thyristor Package: T = TO-220AB 5 Type of silicon: S = converter grade 08 = 800 VVoltage code x 100 = V_{RRM} 12 = 1200 V **FullPAK** Environmental digit:

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-16TTS08FP-M3	50	1000	Antistatic plastic tubes			
VS-16TTS12FP-M3	50	1000	Antistatic plastic tubes			

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

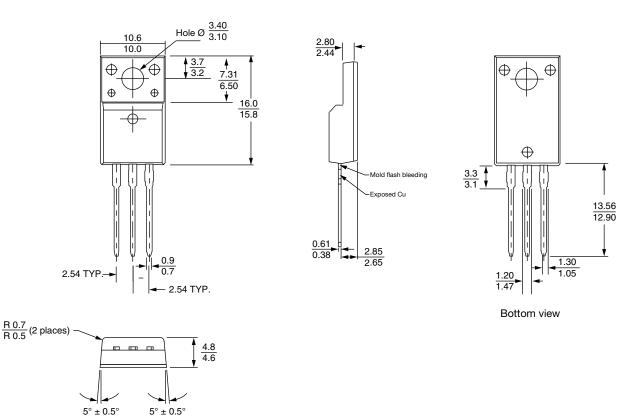
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96155</u>					
Part marking information <u>www.vishay.com/doc?95456</u>					



Vishay Semiconductors

3L TO-220 FullPAK

DIMENSIONS in millimeters



Notes

- (1) All dimensions are in mm
- (2) Package body size exclude mold flash and burrs. Moldflash should be less than 6 mils



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.